

[IEEE HOME](#) | [SEARCH IEEE](#) | [SHOP](#) | [WEB ACCOUNT](#) | [CONTACT IEEE](#)[Membership](#) [Publications/Services](#) [Standards](#) [Conferences](#) [Careers/Jobs](#)**IEEE Xplore®**
RELEASE 1.4Welcome
United States Patent and Trademark Office[Help](#) [FAQ](#) [Terms](#) [IEEE Peer Review](#) [Quick Links](#)

Welcome to IEEE Xplore®

[SEARCH RESULTS](#) [\[PDF Full-Text \(360 KB\)\]](#)[DOWNLOAD CITATION](#)

- ☐ Home
- ☐ What Can I Access?
- ☐ Log-out

Tables of Contents

- ☐ Journals & Magazines
- ☐ Conference Proceedings
- ☐ Standards

Search

- ☐ By Author
- ☐ Basic
- ☐ Advanced

Member Services

- ☐ Join IEEE
- ☐ Establish IEEE Web Account
- ☐ Access the IEEE Member Digital Library

 [Print Format](#)

Implementation of high-side, high-voltage RESUR LDMOS in a sub-half micron smart power technology

Zhu, R. Parthasarathy, V. Khemka, V. Bose, A. Roggenbauer, T.
SPS, Motorola Inc., Mesa, AZ;

This paper appears in: Power Semiconductor Devices and ICs, 2001. ISPS '01. Proceedings of the 13th International Symposium on 06/04/2001 -06/07/2001, 2001

Location: Osaka, Japan

On page(s): 403-406

2001

References Cited: 6

Number of Pages: xxxi+467

INSPEC Accession Number: 7092179

Abstract:

55 V high-side RESURF LDMOS has been integrated successfully in 0.35 μm smart power technology by carefully arranging the lateral doping profile. This device has $R_{\text{ds, on}}$ area of 0.55 $\text{m}\Omega\cdot\text{cm}^2$ with excellent safe operating area. With proper device terminal biasing scheme, this device can also be used as an isolated device. Techniques and issues related to the isolation is considered and discussed.

Index Terms:

doping profiles isolation technology power MOSFET power integrated circuits 0.35 μm 55 V device isolation high-side high-voltage RESURF LDMOS transistor lateral doping profile safe operating area smart power technology terminal biasing

Documents that cite this document

Select link to view other documents in the database that cite this one.

[SEARCH RESULTS](#) [\[PDF Full-Text \(360 KB\)\]](#)[DOWNLOAD CITATION](#)

[Home](#) | [Log-out](#) | [Journals](#) | [Conference Proceedings](#) | [Standards](#) | [Search by Author](#) | [Basic Search](#) | [Advanced Search](#) | [Join IEEE](#) | [Web Account](#) | [New this week](#) | [OPAC Linking Information](#) | [Your Feedback](#) | [Technical Support](#) | [Email Us](#) | [No Robots Please](#) | [Release Notes](#) | [IEEE Online Publications](#) | [Help](#) | [FAQ](#) | [Terms](#) | [Back to Top](#)

Copyright © 2003 IEEE — All rights reserved